WPT2F06

PNP, General Purpose Transistors

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Descriptions

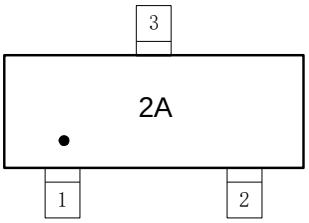
The WPT2F06 is designed for general purpose amplifier applications. Standard products are Pb-free and Halogen-free

SOT-23

Features

- Complementary to WNT2F04
- Collector Current: I_C=-0.2A

(Top View)



Marking :2A

1: BASE
2: EMITTER
3: COLLECTOR

Order information

Device	Package	Shipping
WPT2F06-3/TR	SOT-23	3000/Reel&Tape

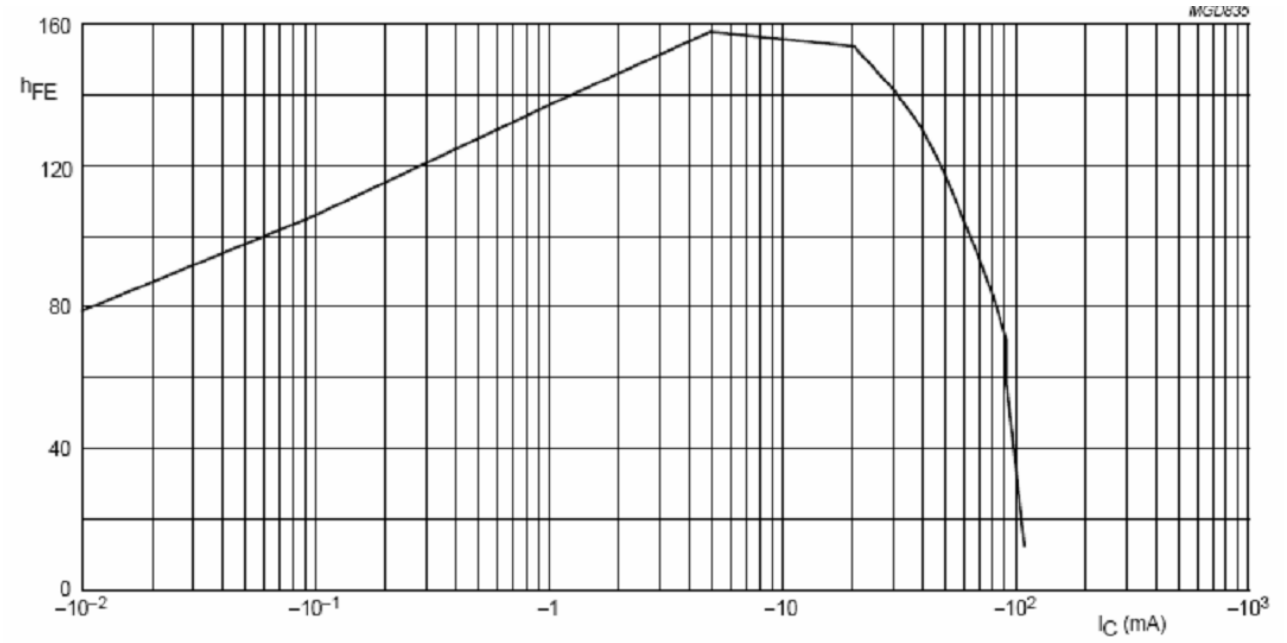
Absolute maximum ratings

Parameter	Symbol	Value	Unit
Collector-emitter Voltage	V_{CEO}	-40	V
Collector-base Voltage	V_{CBO}	-40	V
Emitter-base Voltage	V_{EBO}	-5	V
Continues Collector Current	I_C	-200	mA
Collector Power Dissipation	P_C	200	mW
Thermal Resistance From Junction To Ambient	$R_{\Theta JA}$	625	°C /W
Junction Temperature	T_J	150	°C
Storage Temperature Range	T_{stg}	-55~150	°C

Electronics Characteristics (Ta=25°C, unless otherwise noted)

Parameter	Symbol	Test Conditions	Min.	Typ.	Max.	Unit
Collector-emitter breakdown voltage	BV_{CEO}	I_C=-1mA, I_B=0mA	-40			V
Collector-base breakdown voltage	BV_{CBO}	I_C=10uA, I_E=0mA	-40			V
Emitter-base breakdown voltage	BV_{EBO}	I_E=-10uA, I_C=0mA	-5			V
Collector cutoff current	I_{CEX}	V_{CE}=-30V,$V_{EB(OFF)}$=-3V			-50	nA
Collector cutoff current	I_{CBO}	V_{CB}=-40V, I_E=0A			-100	nA
Emitter cutoff current	I_{EBO}	V_{EB}=-5V, I_C=0A			-100	nA
Collector-emitter saturation voltage	$V_{CE(sat)}$	I_C=-50mA, I_B=-5mA			-0.4	V
Base-emitter saturation voltage	$V_{BE(sat)}$	I_C=-50mA, I_B=-5mA			-0.95	V
DC current gain	h_{FE}	I_C=-10mA , V_{CE}=-1V	100		300	
	h_{FE}	I_C=-50mA , V_{CE}=-1V	60			
	h_{FE}	I_C=-100mA , V_{CE}=-1V	30			
Transition frequency	f_T	V_{CE}=-20V,I_C=-10mA, f=100MHz	250			MHz
Noise figure	NF	I_C=-100μA; V_{CE}=-5V; R_S=1 kΩ; f=10Hz to15.7 kHz			4	dB
Delay time	t_d	V_{CC}=-3V, $V_{BE(off)}$=-0.5V			35	ns
Rise time	t_r	I_C=-10mA,I_{B1}=-1mA			35	ns
Storage time	t_s	V_{CC}=-3V, I_C=-10mA,			225	ns
Fall time	t_f	I_{B1}= I_{B2}=-1mA			75	ns

Typical characteristics (Ta=25°C, unless otherwise noted)

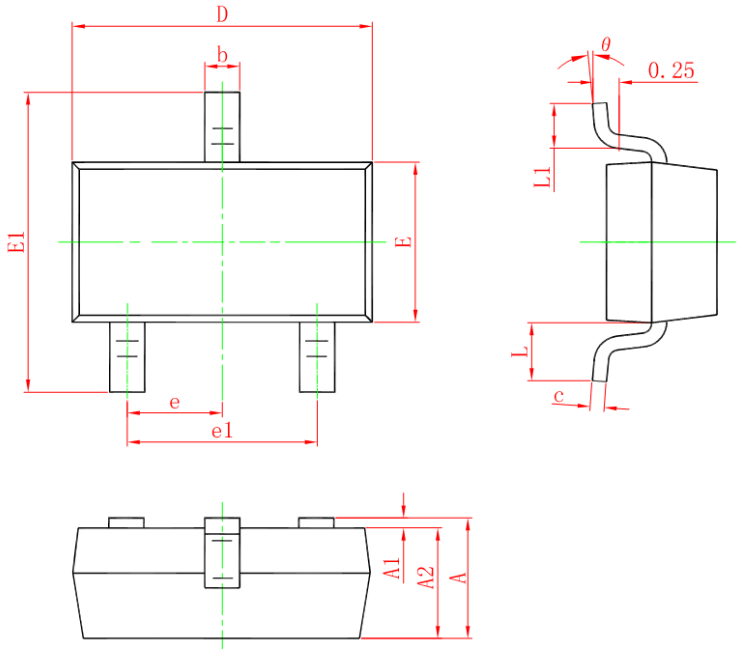


V_{CE} = −1 V.

DC current gain; typical values.

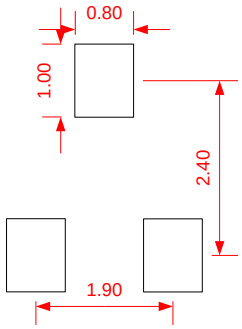
Package outline dimensions

SOT-23



Symbol	Dimensions in millimeter		
	Min.	Typ.	Max.
A	0.900	1.025	1.150
A1	0.000	0.500	0.100
A2	0.900	0.975	1.050
b	0.300	0.400	0.500
c	0.080	0.115	0.150
D	2.800	2.900	3.000
E	1.200	1.300	1.400
E1	2.250	2.400	2.550
e	0.950TYP		
e1	1.800	1.900	2.000
L	0.500REF		
L1	0.300	0.400	0.500
θ	0°	4°	8°

Recommend PCB Layout (Unit: mm)



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